

ACTS04MS

Radiation Hardened Hex Inverter

FN3383 Rev.1.00 January 1996

Features

- Devices QML Qualified in Accordance with MIL-PRF-38535
- Detailed Electrical and Screening Requirements are Contained in SMD# 5962-96712 and Intersil's QM Plan
- 1.25 Micron Radiation Hardened SOS CMOS
- Total Dose >300K RAD (Si)
- Single Event Upset (SEU) Immunity: <1 x 10⁻¹⁰ Errors/ Bit/Day (Typ)
- SEU LET Threshold>100 MEV-cm²/mg
- Dose Rate Upset>10¹¹ RAD (Si)/s, 20ns Pulse
- Dose Rate Survivability>10¹² RAD (Si)/s, 20ns Pulse
- · Latch-Up Free Under Any Conditions
- Military Temperature Range-55°C to +125°C
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range 4.5V to 5.5V
- · Input Logic Levels
 - VIL = 0.8V Max
 - VIH = VCC/2 Min
- Input Current \leq 1 μ A at VOL, VOH
- Fast Propagation Delay14ns (Max), 9ns (Typ)

Description

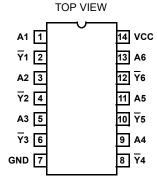
The Intersil ACTS04MS is a Radiation Hardened Hex Inverter.

The ACTS04MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of radiation hardened, high-speed, CMOS/SOS Logic Family.

The ACTS04MS is supplied in a 14 lead Ceramic Flatpack (K suffix) or a Ceramic Dual-In-Line Package (D suffix).

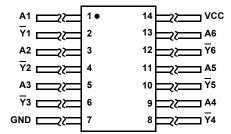
Pinouts

14 PIN CERAMIC DUAL-IN-LINE MIL-STD-1835 DESIGNATOR CDIP2-T14, LEAD FINISH C



14 PIN CERAMIC FLATPACK MIL-STD-1835 DESIGNATOR CDFP3-F14, LEAD FINISH C

TOP VIEW



TRUTH TABLE

INPUTS	OUTPUTS	
An	Yn	
L	Н	
Н	L	

NOTE: L = Logic Level Low, H = Logic level High

Functional Diagram



Ordering Information

PART NUMBER	TEMPERATURE RANGE	SCREENING LEVEL	PACKAGE
5962F9671201VCC	-55°C to +125°C	MIL-PRF-38535 Class V	14 Lead SBDIP
5962F9671201VXC	-55°C to +125°C	MIL-PRF-38535 Class V	14 Lead Ceramic Flatpack
ACTS04D/Sample	25°C	Sample	14 Lead SBDIP
ACTS04K/Sample	25°C	Sample	14 Lead Ceramic Flatpack
ACTS04HMSR	25°C	Die	Die



Die Characteristics

DIE DIMENSIONS:

88 mils x 88 mils 2240mm x 2240mm

METALLIZATION:

Type: AlSi

Metal 1 Thickness: 7.125kÅ ±1.125kÅ Metal 2 Thickness: 9kÅ ±1kÅ

Metallization Mask Layout

GLASSIVATION:

Type: SiO₂

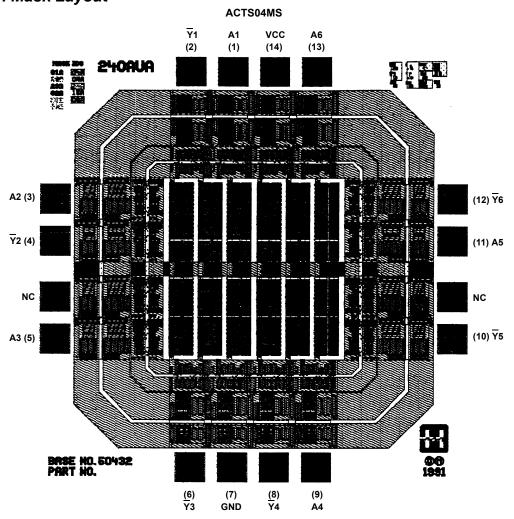
Thickness: 8kÅ ±1kÅ

WORST CASE CURRENT DENSITY:

 $< 2.0 \times 10^5 \text{ A/cm}^2$

BOND PAD SIZE:

4.3 mils x 4.3 mils > 110μm x 110μm



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